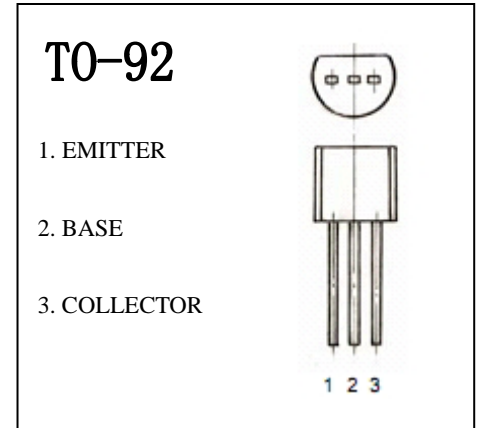


深圳市晶泰源电子有限公司

MPSA44 TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	500	V
VCEO	Collector-Emitter Voltage	400	V
VEBO	Emitter-Base Voltage	6	V
IC	Collector Current	0.3	A
PC	Collector Power Dissipation	625	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	500			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	400			V
Emitter-base breakdown voltage	V(BR)EBO	IC=100uA, IC=0	6			V
Collector cut-off current	ICBO	VCB=400V, IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB=4V, IC=0			0.1	μA
DC current gain	HFE	Vce=10V, IC=1mA	40		300	
Collector-emitter saturation voltage	VCE(sat)	IC=10mA, IB=1mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=10mA, IB=1mA			0.75	V
Collector output capacitance	Cob	VCB=20V, IE=0, f=1MHz			7	pF

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